# 2.5V Drive Nch MOS FET **RJU003N03**

#### Structure

Silicon N-channel MOS FET

## ● Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

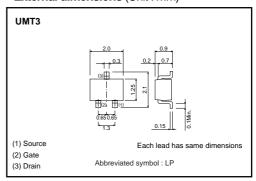
## Applications

Switching

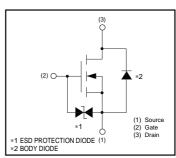
## ●Packaging specifications and hFE

	Package	Taping
Туре	Code	T106
	Basic ordering unit (pieces)	3000
RJU003N03	0	

## ●External dimensions (Unit : mm)



#### •Inner circuit



## ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit		
Drain-source voltage		V <sub>DSS</sub>	30	V		
Gate-source voltage		V <sub>GSS</sub>	±12	V		
Drain current	Continuous	ID	±300	mA		
	Pulsed	IDP *1	±1.2	Α		
Total power dissipation		P <sub>D</sub> *2	200	mW		
Channel temperature		Tch	150	°C		
Range of storage temperature		Tstg	-55 to +150	°C		

#### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

<sup>\*</sup> Each terminal mounted on a recommended land

<sup>\*1</sup> Pw≤10µs, Duty cycle≤1% \*2 Each terminal mounted on a recommended land

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	Vgs=±12V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	٧	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.8	_	1.5	٧	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	-	0.8	1.1	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 4.5V
		-	0.9	1.3	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 4V
		-	1.4	1.9	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub> *	0.4	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 300mA
Input capacitance	Ciss	_	24	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	11	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	5	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	6	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	4	_	ns	ID= 150mA
Turn-off delay time	t <sub>d (off)</sub> *	_	9	_	ns	V <sub>GS</sub> = 4V R <sub>L</sub> =100Ω
Fall time	t <sub>f</sub> *	_	32	_	ns	R <sub>G</sub> =10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	-	1.2	V	I <sub>S</sub> = 200mA, V <sub>GS</sub> =0V

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